At page 2, line 13, please delete "and".

At page 2, line 13, after "(TaN)", please insert --, molybdenum silicide (MoSi$_2$), and tantalum silicide (TaSi$_2$)--.

At page 2, line 16, please delete "tantalum (Ta), molybdenum silicide (MoSi),".

At page 2, lines 16-17, please replace "silicide (TaSi)" with --(Ta)--.

At page 2, line 18, please replace "Previous" with --Previously--.

At page 2, line 23, please replace "necessary" with --desirable--.

At page 2, line 22, please delete "key".

At page 3, line 8, please delete "the incorporation of".

At page 3, line 9, please replace "into a workable process that is scalable for future CMOS technologies" with --in CMOS circuits--.

At page 8, line 18, please replace "a CMOS structure" with --PMOS and NMOS devices--.

At page 11, line 3, please delete "or work function".

At page 11, line 7, please replace "i.e." with --e.g.--.

At page 11, line 17, please delete "region".

At page 11, lines 20 and 21, please replace "masking" with --mask--.

At page 12, line 6, please replace "work function" with --Fermi level--.

At page 12, line 11, please replace "work function" with --Fermi level--.

At page 12, line 20, please delete "or optimum".

At page 13, line 6, please replace "work function" with --Fermi level--.

At page 14, lines 1 and 6, please replace "P-well" with --P-type well--.